

Power-off Isolation, 6 Ω , 1.8 V to 5.5 V, SPDT Analog Switch (2:1 Multiplexer)

DESCRIPTION

The DG4599E is a high performance single-pole, double-throw (SPDT) analog switch designed for 1.8 V to 5.5 V operation with a single power rail.

Fabricated with high density CMOS technology, the device achieves low on resistance of 6 Ω and switch off capacitance of 7 pF at a 5 V power supply and low power consumption, and fast switching speeds.

The DG4599E features break before make switching performance. It can handle both analog and digital signals and permits signals with amplitudes of up to V_{+} to be transmitted in either direction.

A power-off protection circuit is built into the switch to prevent an abnormal current path through the signal pins during the power-off condition. The part can withstand greater than 7 kV ESD (human body model). The DG4599E is available in the compact SC-70-6L package.

FEATURES

- Low switch on-resistance (6 Ω)
- +1.8 V to +5.5 V single supply operation
- Isolation in powered-off mode
- Low voltage logic control
- Control logic inputs can go over V_{+}
- Low parasitic capacitance
- Break before make switching
- Latch-up performance exceeds 200 mA per JESD 78
- High ESD rating
 - 7000 V human body model (JS-001)
 - 1000 V charge device model (JS-002)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



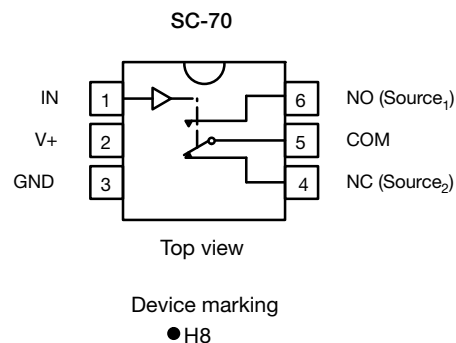
Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Battery powered devices
- Consumer and computing
- Instrumentation
- Medical equipment
- Control and automation

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE		
LOGIC	NC	NO
0	On	Off
1	Off	On

Notes

- Logic "0" \leq 0.8 V
- Logic "1" \geq 2.4 V

ORDERING INFORMATION		
TEMP. RANGE	PACKAGE	PART NUMBER
-40 $^{\circ}$ C to +85 $^{\circ}$ C	SC-70-6	DG4599EDL-T1-GE3



ABSOLUTE MAXIMUM RATINGS				
PARAMETER			LIMIT	UNIT
V+, COM, NC, NO, IN reference to GND			-0.3 to 6	V
Continuous current (any terminal)			± 50	mA
Peak current (pulsed at 1 ms, 10 % duty cycle)			± 200	
Storage temperature			-65 to +150	°C
Power dissipation (packages) ^a	6-pin SC-70 ^b		250	mW
ESD / HBM	JS-001		7000	V
ESD / CDM	JS-002		1000	
Latch up	Per JEDEC78 with 1.5 x voltage clamp		200	mA

Notes

- a. All leads welded or soldered to PC board
- b. Derate 3.1 mW/°C above 70 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+ = 5 V)								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 5 V, ± 10 % VIN = 0.8 V or 2.4 V ^e	TEMP. ^a	LIMITS -40 °C to +85 °C			UNIT	
				MIN. ^b	TYP. ^c	MAX. ^b		
Analog Switch								
Analog signal range ^d	V _{NO} , V _{NC} V _{COM}		Full	0	-	V+	V	
Drain-source on-resistance ^d	R _{DS(on)}	V+ = 4.5 V, V _{COM} = 3 V, I _{NO} , I _{NC} = 10 mA	Room	-	6	60	Ω	
			Full	-	8	65		
R _{DS(on)} flatness ^d	R _{DS(on)} flatness	V+ = 5 V, V _{COM} = 1.5 V, 3.5 V, I _{NO} , I _{NC} = 10 mA	Room	-	0.4	-	Ω	
R _{DS(on)} match ^d	ΔR _{DS(on)}	V+ = 4.5 V, V _{COM} = 3 V, I _{NO} , I _{NC} = 10 mA	Room	-	0.04	2		
Switch-off leakage current ^f	I _{NO(off)} , I _{NC(off)}	V+ = 5.5 V, V _{NO} , V _{NC} = 1 V / 4.5 V, V _{COM} = 4.5 V / 1 V	Room	-1.5	-	1.5	nA	
			Full	-4	-	4		
	Room		-1	-	1			
	Full		-4	-	4			
Channel-on leakage current ^f	I _{COM(on)}	V+ = 5.5 V, V _{NO} , V _{NC} = V _{COM} = 1 V / 4.5 V	Room	-1	-	1	μA	
			Full	-4	-	4		
Power-down leakage	I _{PD}	V+ = 0 V, V _{COM} = 5 V, NO/NC open, V _{IN} = GND	Full	-	-	5	μA	
		V+ = 0 V, V _{NO} , V _{NC} = 5 V, COM open, V _{IN} = GND	Full	-	-	5		
Digital Control								
Input high voltage	V _{INH}		Full	2.4	-	-	V	
Input low voltage	V _{INL}		Full	-	-	0.8		
Input capacitance ^d	C _{IN}		Full	-	6	-	pF	
Input current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	-1	-	1	μA	
Dynamic Characteristics								
Turn-on time ^d	t _{ON}	V _{NO} or V _{NC} = 3 V, R _L = 300 Ω, C _L = 35 pF	Room	-	10	30	ns	
			Full	-	-	40		
Turn-off time ^d	t _{OFF}		Room	-	8	25		
			Full	-	-	30		
Break-before-make time ^d	t _{BBM}			Room	1	-		-
Charge injection ^d	Q _{INJ}		C _L = 1 nF, V _{GEN} = 0 V, V _{NO} , V _{NC} = 0 V, R _{GEN} = 0 Ω	Room	-	1		-
Off-isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room	-	-78	-	dB	
Crosstalk ^d	X _{TALK}		Room	-	-77	-		
			Room	-	7	-		
NO, NC off capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	7	-	pF	
			Room	-	7	-		
Channel-on capacitance ^d	C _{ON}		Room	-	13	-		
Power Supply								
Power supply current ^d	I+	V _{IN} = 0 V or V+	Full	-	0.004	1	μA	



SPECIFICATIONS (V+ = 3 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 3 V, ± 10 % VIN = 0.4 V or 2 V ^e	TEMP. ^a	LIMITS -40 °C to +85 °C			UNIT
				MIN. ^b	TYP. ^c	MAX. ^b	
Analog Switch							
Analog signal range ^d	V _{NO} , V _{NC} V _{COM}		Full	0	-	V+	V
Drain-source on-resistance ^d	R _{DS(on)}	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA	Room	-	13	95	Ω
			Full	-	15	105	
R _{DS(on)} flatness ^d	R _{DS(on)} flatness	V+ = 3 V, V _{COM} = 0 V to V+, I _{NO} , I _{NC} = 10 mA	Room	-	1.4	-	
R _{DS(on)} match ^d	ΔR _{DS(on)}	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA	Room	-	0.03	2	
Switch-off leakage current ^f	I _{NO(off)} , I _{NC(off)}	V+ = 3.3 V, V _{NO} , V _{NC} = 1 V / 3 V, V _{COM} = 3 V / 1 V	Room	-400	-	400	pA
			Full	-4	-	4	nA
	Room		-800	-	800	pA	
	Full		-8	-	8	nA	
Channel-on leakage current ^f	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 1 V / 3 V	Room	-800	-	800	pA
			Full	-8	-	8	nA
Digital Control							
Input high voltage	V _{INH}		Full	2	-	-	V
Input low voltage	V _{INL}		Full	-	-	0.4	
Input capacitance ^d	C _{IN}		Full	-	6	-	pF
Input current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	-1	-	1	μA
Dynamic Characteristics							
Turn-on time ^d	t _{ON}	V _{NO} or V _{NC} = 2 V, R _L = 300 Ω, C _L = 35 pF	Room	-	13	45	ns
			Full	-	-	55	
Turn-off time ^d	t _{OFF}		Room	-	9	35	
			Full	-	-	40	
Break-before-make time ^d	t _{BBM}		Room	1	-	-	
Charge injection ^d	Q _{INJ}		C _L = 1 nF, V _{GEN} = 0 V, V _{NO} , V _{NC} = 0 V, R _{GEN} = 0 Ω	Room	-	0.9	
Off-isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room	-	-78	-	dB
Crosstalk ^d	X _{TALK}		Room	-	-77	-	
NO, NC off capacitance ^d	C _{NO(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	7	-	pF
	C _{NC(off)}		Room	-	7	-	
Channel-on capacitance ^d	C _{ON}		Room	-	14	-	
Power Supply							
Power supply current ^d	I+	V _{IN} = 0 V or V+	Full	-	0.002	1	μA



SPECIFICATIONS (V+ = 2.5 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 2.5 V, ± 10 % VIN = 0.4 V or 2 V ^e	TEMP. ^a	LIMITS -40 °C to +85 °C			UNIT
				MIN. ^b	TYP. ^c	MAX. ^b	
Analog Switch							
Analog signal range ^d	V _{NO} , V _{NC} V _{COM}		Full	0	-	V+	V
Drain-source on-resistance ^d	R _{DS(on)}	V+ = 2.2 V, V _{COM} = 1 V, I _{NO} , I _{NC} = 10 mA	Room Full ^d	- -	23 24	110 120	Ω
R _{DS(on)} flatness ^d	R _{DS(on)} flatness	V+ = 2.5 V, V _{COM} = 0 V to V+, I _{NO} , I _{NC} = 10 mA	Room	-	1.7	-	
R _{DS(on)} match ^d	ΔR _{DS(on)}	V+ = 2.2 V, V _{COM} = 1.2 V, I _{NO} , I _{NC} = 10 mA	Room	-	0.1	2	
Switch-off leakage current ^f	I _{NO(off)} , I _{NC(off)}	V+ = 2.7 V, V _{NO} , V _{NC} = 0.5 V / 1.5 V, V _{COM} = 1.5 V / 0.5 V	Room	-200	-	200	
			Full ^d	-3	-	3	nA
	I _{COM(off)}		Room	-200	-	200	pA
			Full ^d	-3	-	3	nA
Channel-on leakage current ^f	I _{COM(on)}	V+ = 2.7 V, V _{NO} , V _{NC} = V _{COM} = 0.5 V / 1.5 V	Room	-200	-	200	pA
			Full ^d	-3	-	3	nA
Digital Control							
Input high voltage	V _{INH}		Full	2	-	-	V
Input low voltage	V _{INL}		Full	-	-	0.4	
Input capacitance ^d	C _{IN}		Full	-	6	-	pF
Input current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	-1	-	1	μA
Dynamic Characteristics							
Turn-on time ^d	t _{ON}	V _{NO} or V _{NC} = 1.5 V, R _L = 300 Ω, C _L = 35 pF	Room	-	16	50	ns
			Full ^d	-	-	60	
Turn-off time ^d	t _{OFF}		Room	-	10	35	
			Full	-	-	45	
Break-before-make time ^d	t _{BBM}		Room ^d	1	-	-	
Charge injection ^d	Q _{INJ}		C _L = 1 nF, V _{GEN} = 0 V, V _{NO} , V _{NC} = 0 V, R _{GEN} = 0 Ω	Room	-	0.9	
Off-isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room	-	-78	-	dB
Crosstalk ^d	X _{TALK}		Room	-	-77	-	
NO, NC off capacitance ^d	C _{NO(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	7	-	pF
	C _{NC(off)}		Room	-	7	-	
Channel-on capacitance ^d	C _{ON}		Room	-	14	-	
Power Supply							
Power supply current ^d	I+	V _{IN} = 0 V or V+	Full	-	-	1	μA



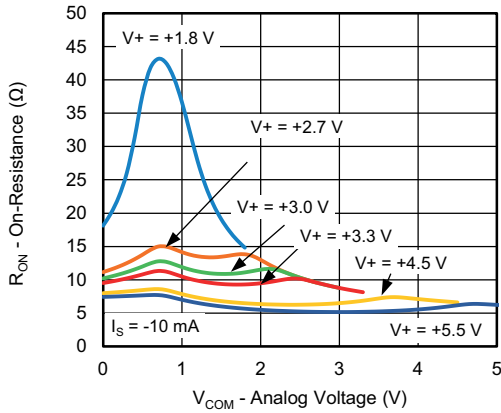
SPECIFICATIONS (V+ = 2 V)								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 2 V, ± 10 % VIN = 0.4 V or 1.6 V ^e	TEMP. ^a	LIMITS -40 °C to +85 °C			UNIT	
				MIN. ^b	TYP. ^c	MAX. ^b		
Analog Switch								
Analog signal range ^d	V _{NO} , V _{NC} V _{COM}		Full	0	-	V+	V	
Drain-source on-resistance ^d	R _{DS(on)}	V+ = 1.8 V, V _{COM} = 1 V, I _{NO} , I _{NC} = 10 mA	Room	-	37	110	Ω	
			Full ^d	-	36	120		
R _{DS(on)} flatness ^d	R _{DS(on)} flatness	V+ = 2 V, V _{COM} = 0 V to V+, I _{NO} , I _{NC} = 10 mA	Room	-	3	-		
R _{DS(on)} match ^d	ΔR _{DS(on)}	V+ = 1.8 V, V _{COM} = 1 V, I _{NO} , I _{NC} = 10 mA	Room	-	0.04	2		
Switch-off leakage current ^f	I _{NO(off)} , I _{NC(off)}	V+ = 2.2 V, V _{NO} , V _{NC} = 0.5 V / 1.5 V, V _{COM} = 1.5 V / 0.5 V	Room	-200	-	200	pA	
			Full ^d	-3	-	3	nA	
	I _{COM(off)}		Room	-200	-	200	pA	
			Full ^d	-3	-	3	nA	
Channel-on leakage current ^f	I _{COM(on)}	V+ = 2.2 V, V _{NO} , V _{NC} = V _{COM} = 0.5 V / 1.5 V	Room	-200	-	200	pA	
			Full ^d	-3	-	3	nA	
Digital Control								
Input high voltage	V _{INH}		Full	1.6	-	-	V	
Input low voltage	V _{INL}		Full	-	-	0.4		
Input capacitance ^d	C _{IN}		Full	-	6	-	pF	
Input current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	-1	-	1	μA	
Dynamic Characteristics								
Turn-on time ^d	t _{ON}	V _{NO} or V _{NC} = 1.5 V, R _L = 300 Ω, C _L = 35 pF	Room	-	21	50	ns	
			Full ^d	-	-	60		
Turn-off time ^d	t _{OFF}		Room	-	13	35		
			Full ^d	-	-	45		
Break-before-make time ^d	t _{BBM}			Room	1	-		-
Charge injection ^d	Q _{INJ}		C _L = 1 nF, V _{GEN} = 0 V, V _{NO} , V _{NC} = 0 V, R _{GEN} = 0 Ω	Room	-	0.8		-
Off-isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room	-	-78	-	dB	
Crosstalk ^d	X _{TALK}		Room	-	-77	-		
NO, NC off capacitance ^d	C _{NO(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	7	-	pF	
	C _{NC(off)}		Room	-	7	-		
Channel-on capacitance ^d	C _{ON}		Room	-	14	-		
Power Supply								
Power supply current ^d	I+	V _{IN} = 0 V or V+	Full	-	-	1	μA	

Notes

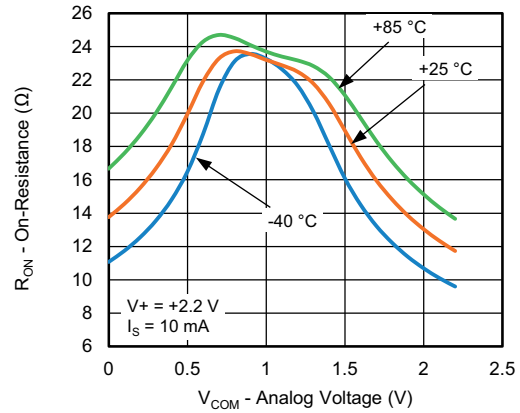
- a. Room = 25 °C, full = as determined by the operating suffix
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- c. Typical values are for design aid only, not guaranteed nor subject to production testing
- d. Guarantee by design, nor subjected to production test
- e. V_{IN} = input voltage to perform proper function
- f. Guaranteed by 5 V leakage testing, not production tested



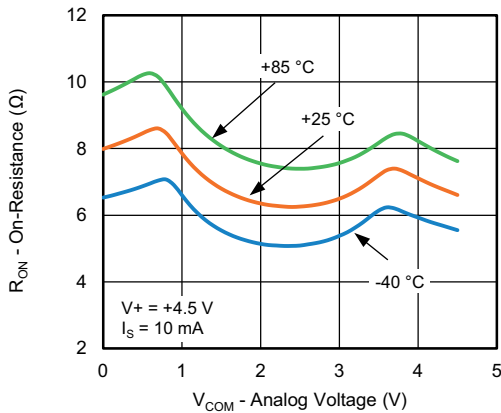
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



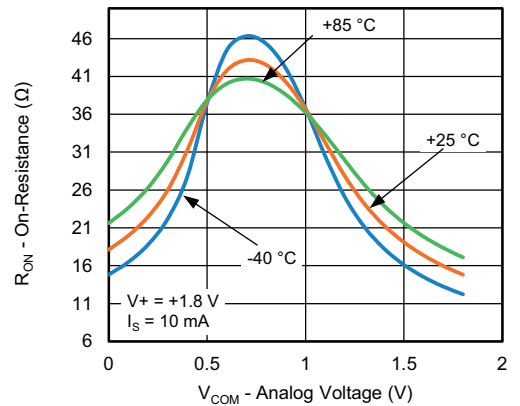
R_{DS(on)} vs. V_{COM} and Supply Voltage



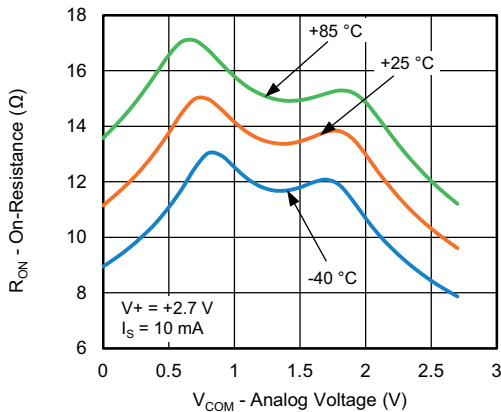
R_{DS(on)} vs. Analog Voltage and Temperature



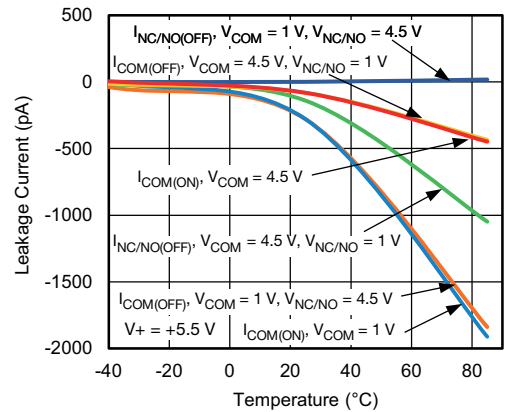
R_{DS(on)} vs. Analog Voltage and Temperature



R_{DS(on)} vs. Analog Voltage and Temperature

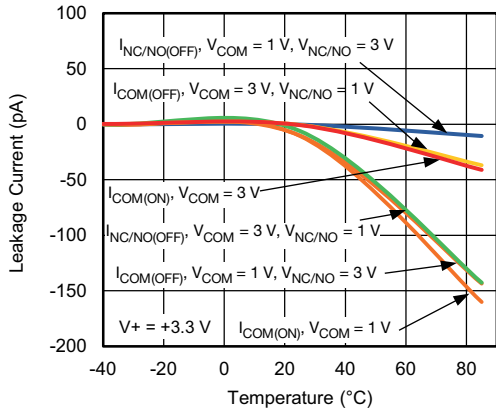


R_{DS(on)} vs. Analog Voltage and Temperature

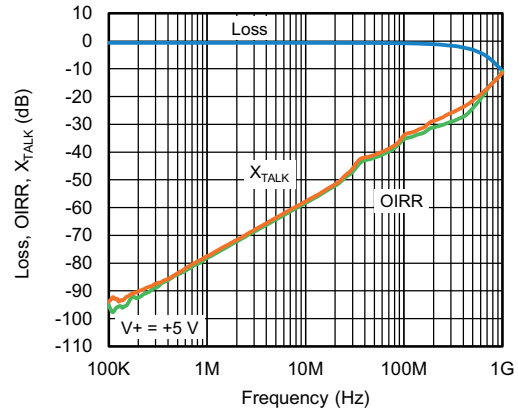


Leakage Current vs. Temperature

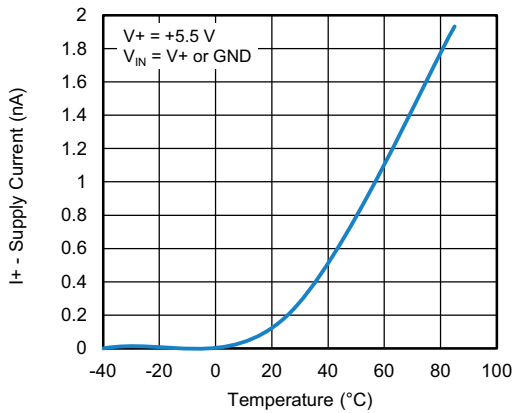
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



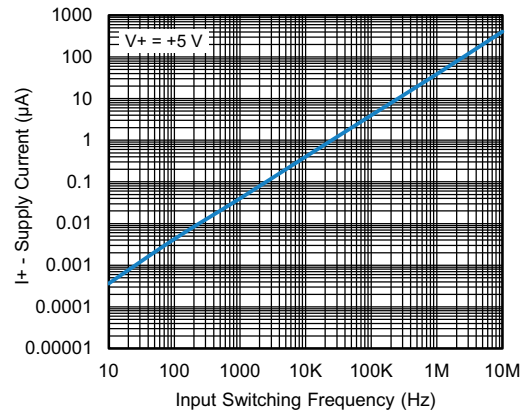
Leakage Current vs. Temperature



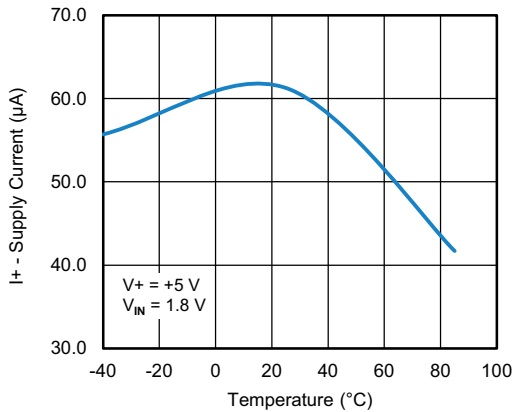
Insertion Loss, Off-Isolation Crosstalk vs. Frequency



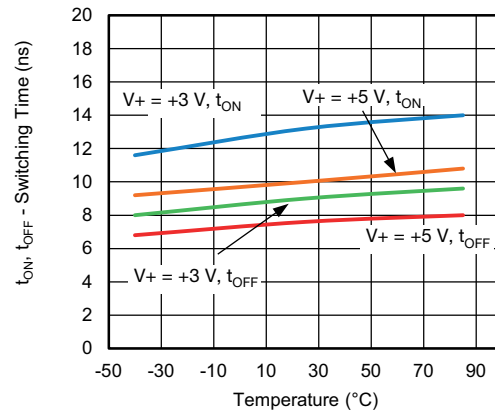
Supply Current vs. Temperature



Supply Current vs. Input Switching Frequency

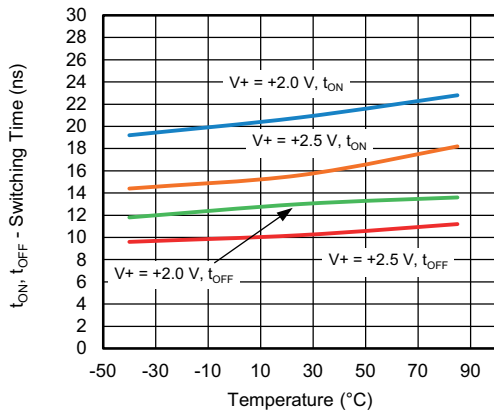


Supply Current vs. Temperature

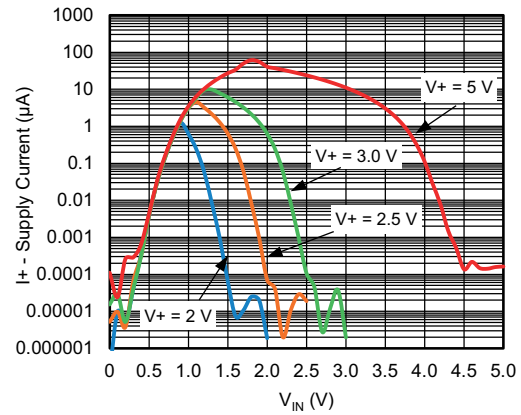


Switching Time vs. Temperature

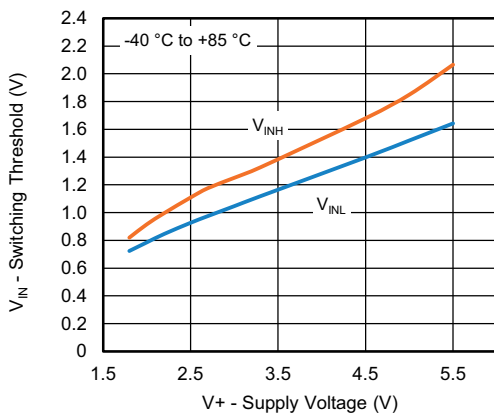
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



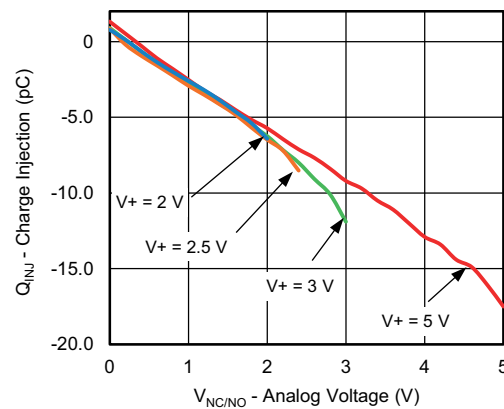
Switching Time vs. Temperature



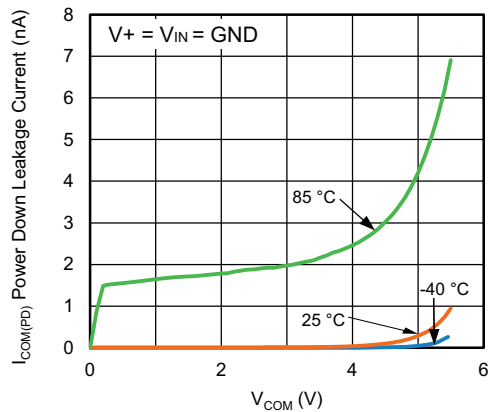
Supply Current vs. Enable Input Voltage



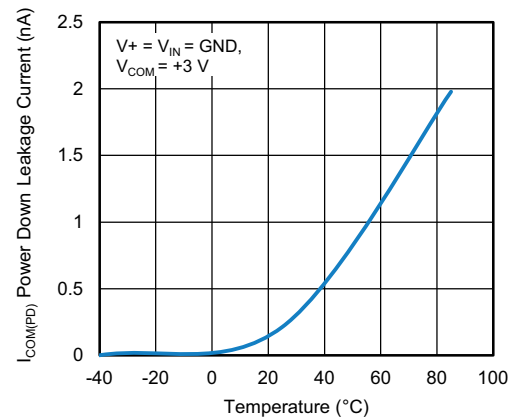
Switching Threshold vs. Supply Voltage



Charge Injection vs. Analog Voltage

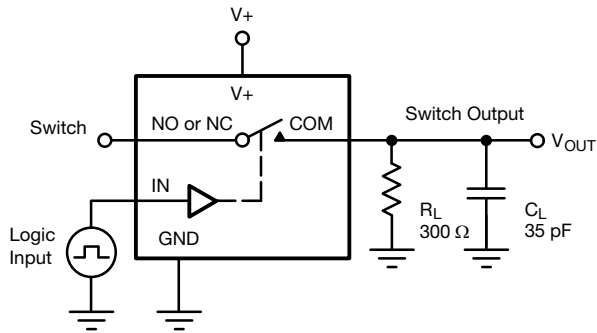


Power Down Leakage Current vs. V_{COM}



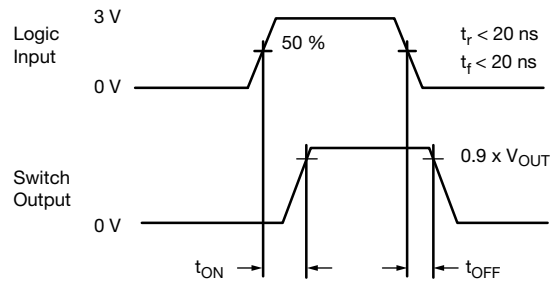
Power Down Leakage Current vs. Temperature

TEST CIRCUITS



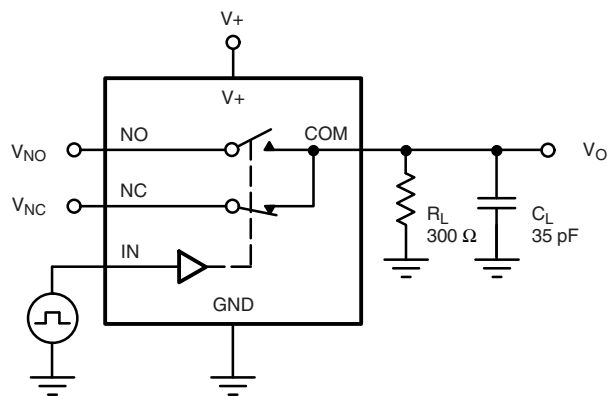
C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = switch on
Logic input waveforms inverted for switches that have the opposite logic sense.

Fig. 1 - Switching Time



C_L (includes fixture and stray capacitance)

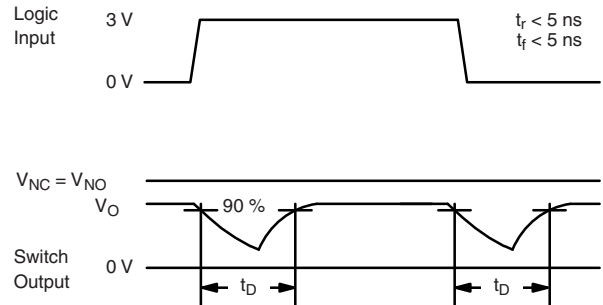
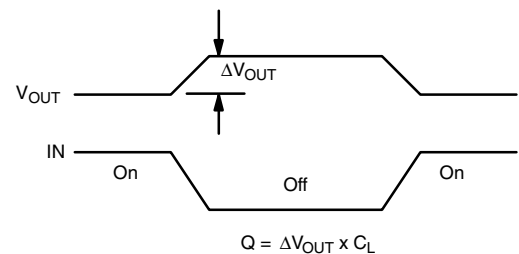
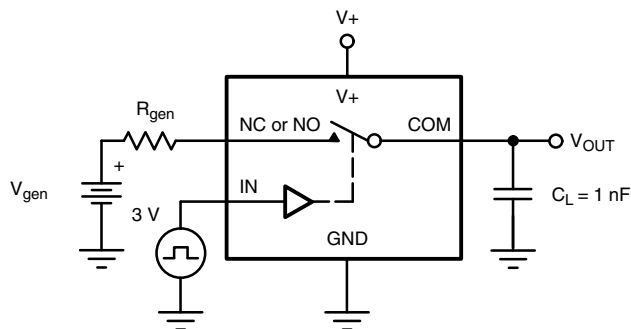


Fig. 2 - Break-Before-Make Interval



IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 3 - Charge Injection

TEST CIRCUITS

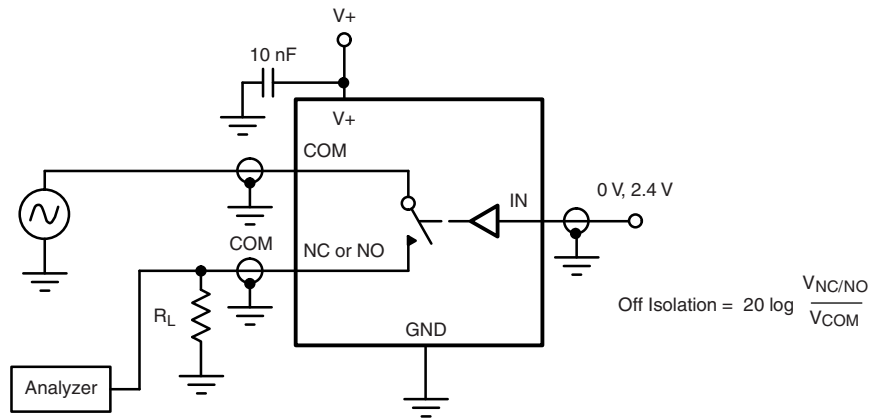


Fig. 4 - Off-Isolation

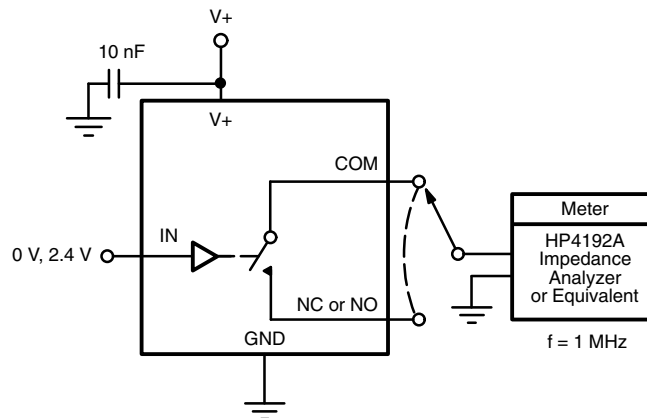


Fig. 5 - Channel Off / On Capacitance

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